

HY1908D-VB Datasheet

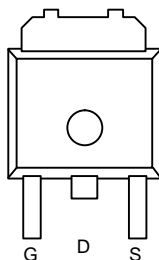
N-Channel 80 V (D-S) MOSFET



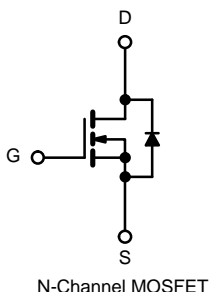
RoHS
COMPLIANT
HALOGEN
FREE

| PRODUCT SUMMARY | | | |
|---------------------|-----------------------------------|--------------------|-----------------------|
| V _{DS} (V) | R _{DS(on)} (Ω) Max. | I _D (A) | Q _g (Typ.) |
| 80 | 0.0050 at V _{GS} = 10 V | 75 ^a | 17.1 nC |
| | 0.0070 at V _{GS} = 6.0 V | 65 ^a | |
| | 0.0087 at V _{GS} = 5.0 V | 54 | |

TO-252



Top View



N-Channel MOSFET

FEATURES

- Trench Power MOSFET
- 100 % R_g and UIS Tested

APPLICATIONS

- Primary Side Switching
- Synchronous Rectification
- DC/AC Inverters
- LED Backlighting

| ABSOLUTE MAXIMUM RATINGS (T _A = 25 °C, unless otherwise noted) | | | | |
|---|------------------------|-----------------------------------|----------------------|------|
| Parameter | | Symbol | Limit | Unit |
| Drain-Source Voltage | | V _{DS} | 80 | V |
| Gate-Source Voltage | | V _{GS} | ± 20 | |
| Continuous Drain Current (T _J = 150 °C) | T _C = 25 °C | I _D | 75 ^a | A |
| | T _C = 70 °C | | 62.7 | |
| | T _A = 25 °C | | 28.6 ^{b, c} | |
| | T _A = 70 °C | | 24.9 ^{b, c} | |
| Pulsed Drain Current (t = 100 μs) | | I _{DM} | 150 | |
| Continuous Source-Drain Diode Current | T _C = 25 °C | I _S | 75 ^a | |
| | T _A = 25 °C | | 4.5 ^{b, c} | |
| Single Pulse Avalanche Current | | I _{AS} | 30 | mJ |
| Single Pulse Avalanche Energy | | E _{AS} | 45 | |
| Maximum Power Dissipation | T _C = 25 °C | P _D | 62.5 | W |
| | T _C = 70 °C | | 40 | |
| | T _A = 25 °C | | 5 ^{b, c} | |
| | T _A = 70 °C | | 3.2 ^{b, c} | |
| Operating Junction and Storage Temperature Range | | T _J , T _{stg} | - 55 to 150 | °C |
| Soldering Recommendations (Peak Temperature) ^{d, e} | | | 260 | |

| THERMAL RESISTANCE RATINGS | | | | |
|---|--------------|-------------------|---------|---------|
| Parameter | | Symbol | Typical | Maximum |
| Maximum Junction-to-Ambient ^{b, f} | t ≤ 10 s | R _{thJA} | 20 | 25 |
| | Steady State | R _{thJC} | 1.5 | 2.0 |

Notes

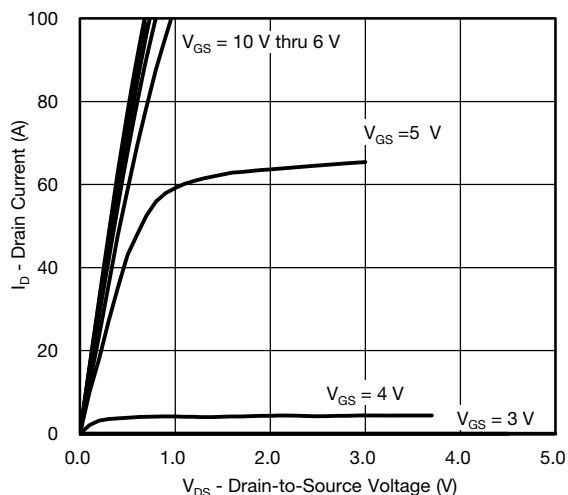
- Package limited.
- Surface mounted on 1" x 1" FR4 board.
- t = 10 s.
- The TO-220 is a leadless package. The end of the lead terminal is exposed copper (not plated) as a result of the singulation process in manufacturing. A solder fillet at the exposed copper tip cannot be guaranteed and is not required to ensure adequate bottom side solder interconnection.
- Rework conditions: manual soldering with a soldering iron is not recommended for leadless components.
- Maximum under steady state conditions is 70 °C/W.

| SPECIFICATIONS (T _J = 25 °C, unless otherwise noted) | | | | | | |
|---|--------------------------------------|---|------|--------|-------|-------|
| Parameter | Symbol | Test Conditions | Min. | Typ. | Max. | Unit |
| Static | | | | | | |
| Drain-Source Breakdown Voltage | V _{DS} | V _{GS} = 0 V, I _D = 250 μA | 80 | | | V |
| V _{DS} Temperature Coefficient | ΔV _{DS} /T _J | I _D = 250 μA | | 37 | | mV/°C |
| V _{GS(th)} Temperature Coefficient | ΔV _{GS(th)} /T _J | | | - 6.1 | | |
| Gate-Source Threshold Voltage | V _{GS(th)} | V _{DS} = V _{GS} , I _D = 250 μA | 2.5 | | 4.0 | V |
| Gate-Source Leakage | I _{GSS} | V _{DS} = 0 V, V _{GS} = ± 20 V | | | ± 100 | nA |
| Zero Gate Voltage Drain Current | I _{DSS} | V _{DS} = 80 V, V _{GS} = 0 V | | | 1 | μA |
| | | V _{DS} = 80 V, V _{GS} = 0 V, T _J = 55 °C | | | 10 | |
| On-State Drain Current ^a | I _{D(on)} | V _{DS} ≥ 5 V, V _{GS} = 10 V | 30 | | | A |
| Drain-Source On-State Resistance ^a | R _{DS(on)} | V _{GS} = 10 V, I _D = 20 A | | 0.0050 | | Ω |
| | | V _{GS} = 6 V, I _D = 15 A | | 0.0070 | | |
| | | V _{GS} = 5.0 V, I _D = 10 A | | 0.0087 | | |
| Forward Transconductance ^a | g _{fs} | V _{DS} = 10 V, I _D = 20 A | | 60 | | S |
| Dynamic ^b | | | | | | |
| Input Capacitance | C _{iss} | V _{DS} = 40 V, V _{GS} = 0 V, f = 1 MHz | | 1855 | | pF |
| Output Capacitance | C _{oss} | | | 950 | | |
| Reverse Transfer Capacitance | C _{rss} | | | 76 | | |
| Total Gate Charge | Q _g | V _{DS} = 40 V,V _{GS} = 10 V, I _D = 10 A | | 35.5 | 54 | nC |
| | | V _{DS} = 40 V, V _{GS} = 6 V, I _D = 10 A | | 22 | 33 | |
| | | V _{DS} = 40 V,V _{GS} = 4.5 V, I _D = 10 A | | 17.1 | 26 | |
| Gate-Source Charge | Q _{gs} | | | 5.3 | | |
| Gate-Drain Charge | Q _{gd} | | | 7.3 | | |
| Output Charge | Q _{oss} | V _{DS} = 40 V, V _{GS} = 0 V | | 57 | 86 | |
| Gate Resistance | R _g | f = 1 MHz | 0.5 | 1.3 | 2 | Ω |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 40 V, R _L = 4 Ω I _D ≅ 10 A, V _{GEN} = 10 V, R _g = 1 Ω | | 12 | 24 | ns |
| Rise Time | t _r | | | 8 | 16 | |
| Turn-Off DelayTime | t _{d(off)} | | | 32 | 64 | |
| Fall Time | t _f | | | 7 | 14 | |
| Turn-On Delay Time | t _{d(on)} | V _{DD} = 40 V, R _L = 4 Ω I _D ≅ 10 A, V _{GEN} = 6.0 V, R _g = 1 Ω | | 14 | 28 | |
| Rise Time | t _r | | | 11 | 22 | |
| Turn-Off DelayTime | t _{d(off)} | | | 30 | 60 | |
| Fall Time | t _f | | | 8 | 16 | |
| Drain-Source Body Diode Characteristics | | | | | | |
| Continuous Source-Drain Diode Current | I _S | T _C = 25 °C | | | 75 | A |
| Pulse Diode Forward Current (t = 100 μs) | I _{SM} | | | | 150 | |
| Body Diode Voltage | V _{SD} | I _S = 5 A | | 0.76 | 1.1 | V |
| Body Diode Reverse Recovery Time | t _{rr} | I _F = 10 A, dI/dt = 100 A/μs, T _J = 25 °C | | 38 | 75 | ns |
| Body Diode Reverse Recovery Charge | Q _{rr} | | | 36 | 70 | nC |
| Reverse Recovery Fall Time | t _a | | | 19 | | ns |
| Reverse Recovery Rise Time | t _b | | | 19 | | |

Notes

- a. Pulse test; pulse width $\leq 300\text{ }\mu\text{s}$, duty cycle $\leq 2\%$.
 b. Guaranteed by design, not subject to production testing.

Stresses beyond those listed under "Absolute Maximum Ratings" may cause permanent damage to the device. These are stress ratings only, and functional operation of the device at these or any other conditions beyond those indicated in the operational sections of the specifications is not implied. Exposure to absolute maximum rating conditions for extended periods may affect device reliability.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Output Characteristics

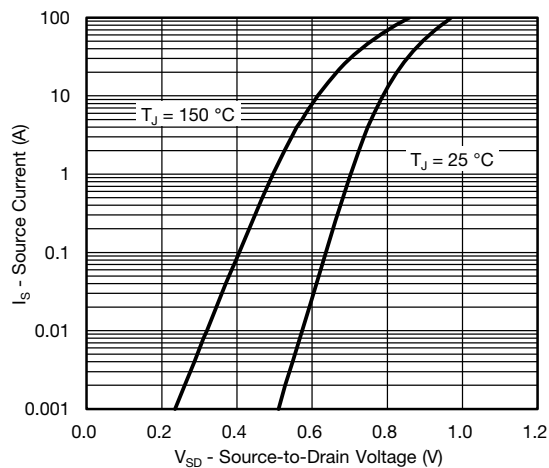
Transfer Characteristics

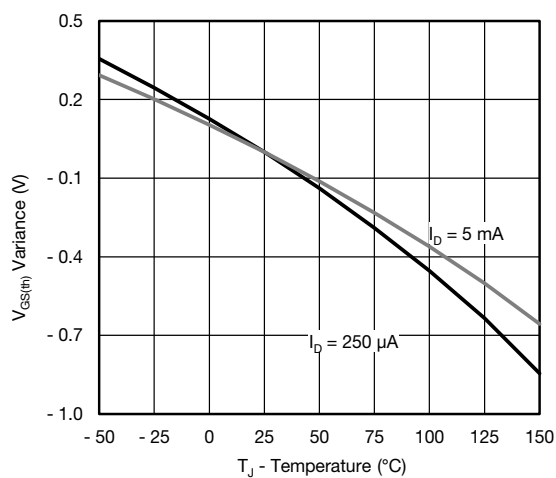
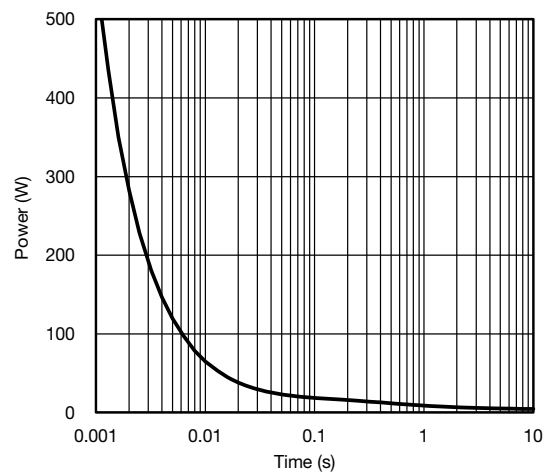
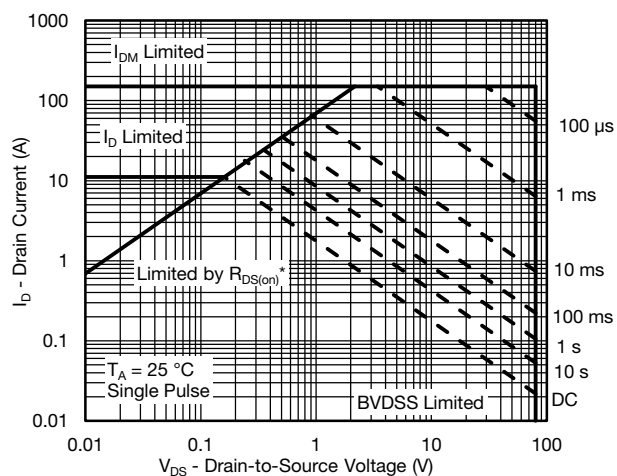
On-Resistance vs. Drain Current

Capacitance

Gate Charge

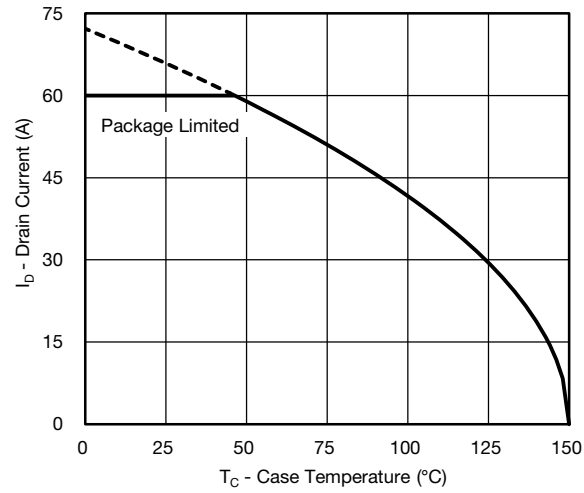
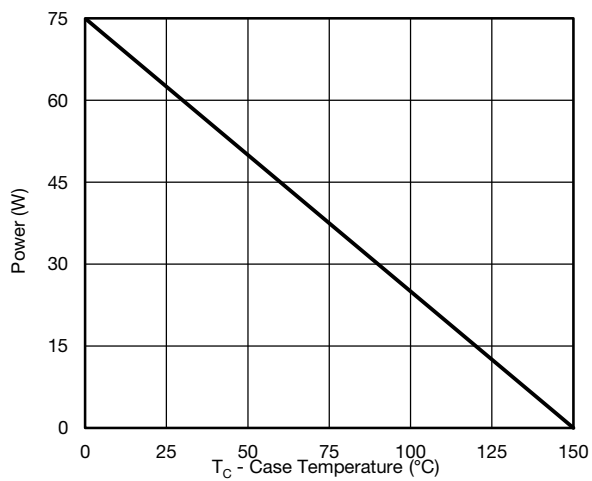
On-Resistance vs. Junction Temperature

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Source-Drain Diode Forward Voltage

On-Resistance vs. Gate-to-Source Voltage

Threshold Voltage

Single Pulse Power, Junction-to-Ambient


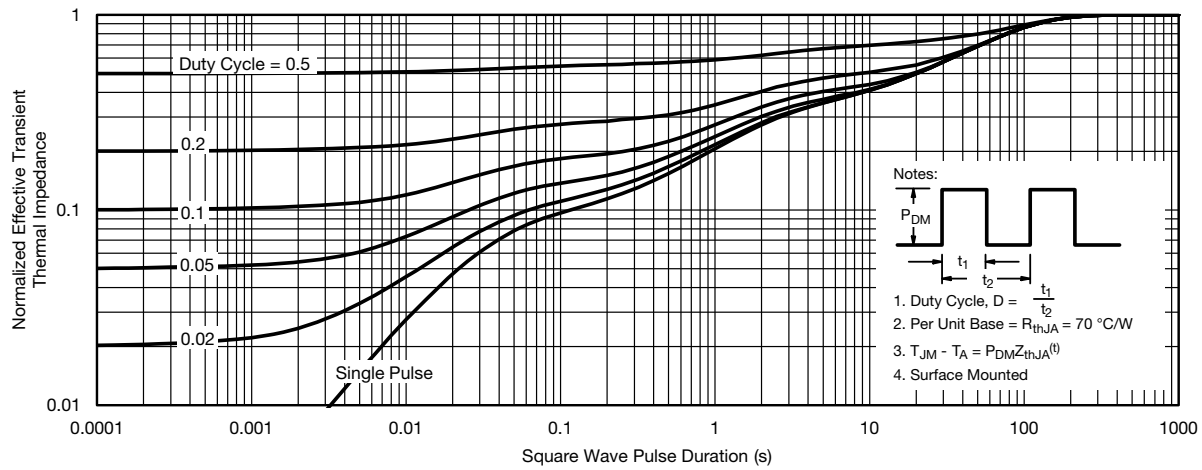
* $V_{GS} >$ minimum V_{GS} at which $R_{DS(on)}$ is specified

Safe Operating Area, Junction-to-Ambient

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Current Derating*

Power, Junction-to-Case

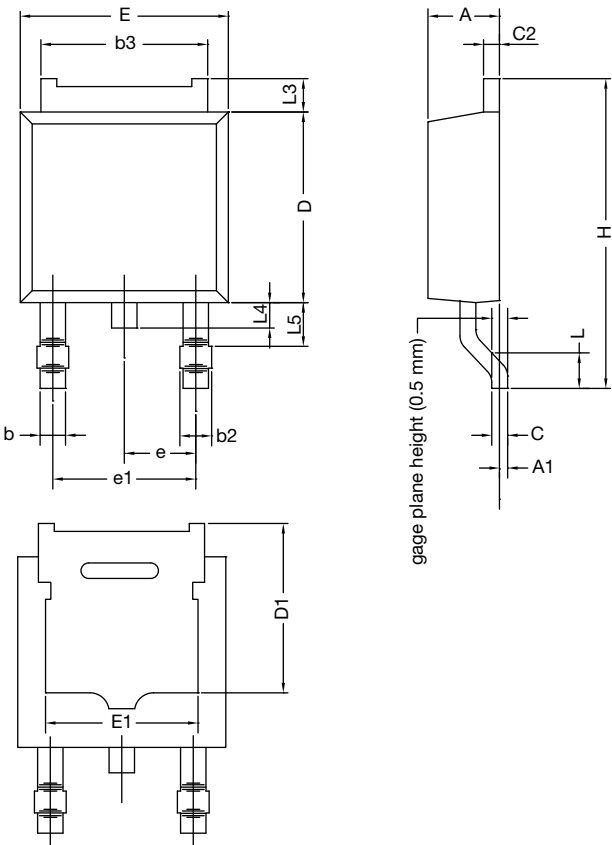
Power, Junction-to-Ambient

* The power dissipation P_D is based on $T_{J(max)} = 150$ °C, using junction-to-case thermal resistance, and is more useful in settling the upper dissipation limit for cases where additional heatsinking is used. It is used to determine the current rating, when this rating falls below the package limit.

TYPICAL CHARACTERISTICS (25 °C, unless otherwise noted)

Normalized Thermal Transient Impedance, Junction-to-Ambient

Normalized Thermal Transient Impedance, Junction-to-Case

TO-252AA CASE OUTLINE

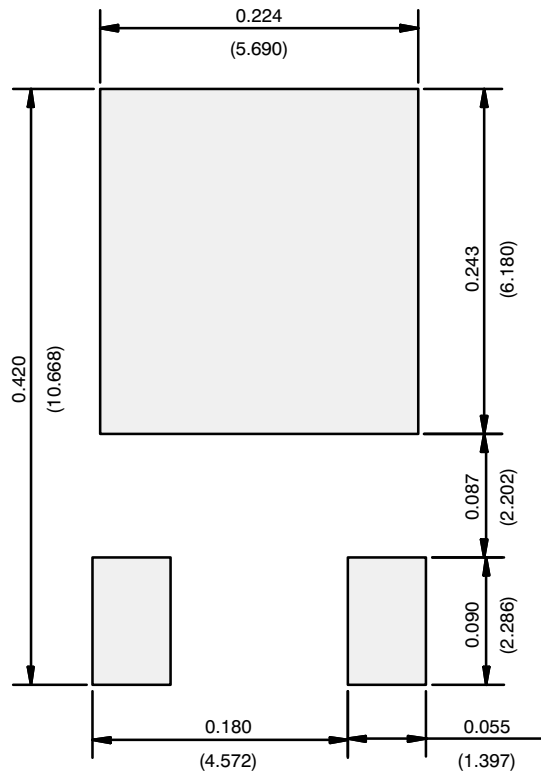


| DIM. | MILLIMETERS | | INCHES | |
|---------------------------------|-------------|-------|-----------|-------|
| | MIN. | MAX. | MIN. | MAX. |
| A | 2.18 | 2.38 | 0.086 | 0.094 |
| A1 | - | 0.127 | - | 0.005 |
| b | 0.64 | 0.88 | 0.025 | 0.035 |
| b2 | 0.76 | 1.14 | 0.030 | 0.045 |
| b3 | 4.95 | 5.46 | 0.195 | 0.215 |
| C | 0.46 | 0.61 | 0.018 | 0.024 |
| C2 | 0.46 | 0.89 | 0.018 | 0.035 |
| D | 5.97 | 6.22 | 0.235 | 0.245 |
| D1 | 5.21 | - | 0.205 | - |
| E | 6.35 | 6.73 | 0.250 | 0.265 |
| E1 | 4.32 | - | 0.170 | - |
| H | 9.40 | 10.41 | 0.370 | 0.410 |
| e | 2.28 BSC | | 0.090 BSC | |
| e1 | 4.56 BSC | | 0.180 BSC | |
| L | 1.40 | 1.78 | 0.055 | 0.070 |
| L3 | 0.89 | 1.27 | 0.035 | 0.050 |
| L4 | - | 1.02 | - | 0.040 |
| L5 | 1.14 | 1.52 | 0.045 | 0.060 |
| ECN: X12-0247-Rev. M, 24-Dec-12 | | | | |
| DWG: 5347 | | | | |

Note

- Dimension L3 is for reference only.

RECOMMENDED MINIMUM PADS FOR DPAK (TO-252)



Recommended Minimum Pads
Dimensions in Inches/(mm)

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